

MICRO ELECTRONICS

PN3568

NPN

SILICON
TRANSISTOR

PN3568 is NPN silicon planar epitaxial transistor designed for amplifier and switching applications for collector current up to 500mA.

T0-92



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V_{CB0}	80V
Collector-Emitter Voltage	V_{CE0}	60V
Emitter-Base Voltage	V_{EB0}	5V
Collector Current	I_C	500mA
Total Power Dissipation	P_{tot}	600mW
Operating Junction & Storage Temperature	T_j, T_{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BV_{CB0}	80		V	$I_C = 100\mu\text{A}$ $I_E = 0$
Collector-Emitter Breakdown Voltage	LV_{CE0}	60		V	$I_C = 10\text{mA}$ $I_B = 0^*$
Emitter-Base Breakdown Voltage	BV_{EB0}	5		V	$I_E = 10\mu\text{A}$ $I_C = 0$
Collector Cutoff Current	I_{CB0}		50	nA	$V_{CB} = 40\text{V}$ $I_E = 0$
D.C. Current Gain	H_{FE}	40			$I_C = 30\text{mA}$ $V_{CE} = 1\text{V}^*$
		40	120		$I_C = 150\text{mA}$ $V_{CE} = 1\text{V}^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.25	V	$I_C = 150\text{mA}$ $I_B = 15\text{mA}^*$
Output Capacitance	C_{ob}		20	pF	$V_{CB} = 10\text{V}$ $f = 1\text{MHz}$
Current Gain-Bandwidth Product	f_T	60	600	MHz	$I_C = 50\text{mA}$ $V_{CE} = 1\text{V}$

* Pulse Test : Pulse Width = 300 μs , Duty Cycle = 2%.

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